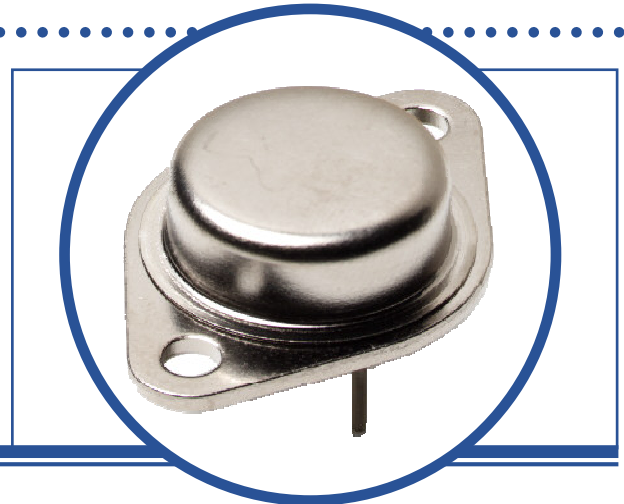


SILICON MULTI-EPITAXIAL NPN TRANSISTOR

BUP52

- Low $V_{CE(SAT)}$, Fast switching.
- Hermetic TO3 Metal package.
- Ideally suited for Motor Control, Switching and Linear Applications
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

V_{CEX}	Collector – Emitter Voltage	$V_{BE} = -1.5\text{V}$	300V
V_{CEO}	Collector – Emitter Voltage		200V
V_{EBO}	Emitter – Base Voltage		10V
I_C	Continuous Collector Current		70A
I_{CM}	Peak Collector Current		90A
P_D	Total Power Dissipation at	$T_C = 25^\circ\text{C}$	300W
		Derate Above 25°C	1.72W/ $^\circ\text{C}$
T_J	Junction Temperature Range		-55 to $+200^\circ\text{C}$
T_{stg}	Storage Temperature Range		-55 to $+200^\circ\text{C}$

THERMAL PROPERTIES

Symbols	Parameters	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction To Case			0.58	$^\circ\text{C/W}$

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

SILICON MULTI-EPITAXIAL NPN TRANSISTOR BUP52

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
I_{CEX}	Collector Cut-Off Current	$V_{CE} = 300\text{V}$ $V_{BE} = -1.5\text{V}$			0.1	mA
		$T_C = 150^\circ\text{C}$			5	
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 8\text{V}$ $I_C = 0$			0.1	
$V_{(BR)CEO}^{(1)}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$	200			V
$V_{CE(sat)}^{(1)}$	Collector-Emitter Saturation Voltage	$I_C = 20\text{A}$ $I_B = 2\text{A}$			0.5	
		$I_C = 40\text{A}$ $I_B = 4\text{A}$			0.6	
		$I_C = 70\text{A}$ $I_B = 14\text{A}$			0.9	
$V_{BE(sat)}^{(1)}$	Base-Emitter Saturation Voltage	$I_C = 20\text{A}$ $I_B = 2\text{A}$			1.1	
		$I_C = 40\text{A}$ $I_B = 5\text{A}$			1.2	
		$I_C = 70\text{A}$ $I_B = 15\text{A}$			1.5	
$h_{FE}^{(1)}$	Forward-current transfer ratio	$I_C = 20\text{A}$ $V_{CE} = 4\text{V}$	20			
		$I_C = 40\text{A}$ $V_{CE} = 4\text{V}$	12			
		$I_C = 70\text{A}$ $V_{CE} = 4\text{V}$	8			

DYNAMIC CHARACTERISTICS

t_s	Storage Time	$I_C = 40\text{A}$ $V_{CC} = 200\text{V}$			1.0	μs
t_f	Fall Time	$I_{B1} = -I_{B2} = 10\text{A}$			0.3	

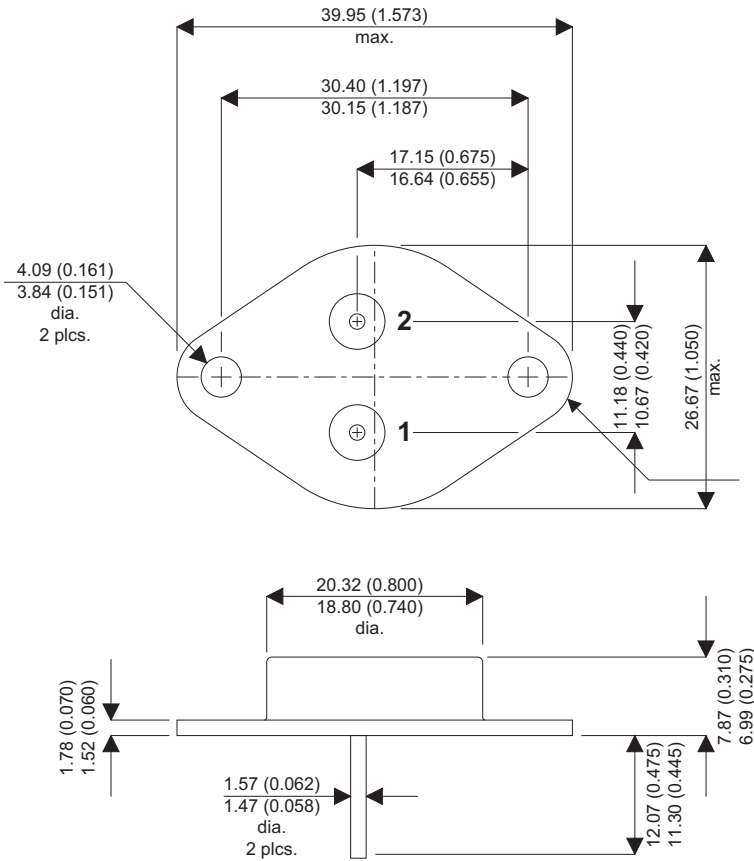
Notes

(1) Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$

SILICON MULTI-EPITAXIAL NPN TRANSISTOR BUP52

MECHANICAL DATA

Dimensions in mm (inches)



TO3 (TO-204AE)

Pin 1 - Base

Pin 2 - Emitter

Case - Collector